To our customers,

Old Company Name in Catalogs and Other Documents

On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: http://www.renesas.com

April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

Send any inquiries to http://www.renesas.com/inquiry.

RENESAS

Notice

1. All information included in this document is current as of the date this document is issued. Such information, however, is subject to change without any prior notice. Before purchasing or using any Renesas Electronics products listed herein, please confirm the latest product information with a Renesas Electronics sales office. Also, please pay regular and careful attention to additional and different information to be disclosed by Renesas Electronics such as that disclosed through our website.
2. Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
3. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part.
4. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
5. When exporting the products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations. You should not use Renesas Electronics products or the technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations.
6. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
7. Renesas Electronics products are classified according to the following three quality grades: "Standard", "High Quality", and "Specific". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below. You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application categorized as "Specific" without the prior written consent of Renesas Electronics. Further, you may not use any Renesas Electronics product for any application for which it is not intended without the prior written consent of Renesas Electronics. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for an application categorized as "Specific" or for which the product is not intended where you have failed to obtain the prior written consent of Renesas Electronics. The quality grade of each Renesas Electronics product is "Standard" unless otherwise expressly specified in a Renesas Electronics data sheets or data books, etc.

   "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots.

   "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; safety equipment; and medical equipment not specifically designed for life support.

   "Specific": Aircraft; aerospace equipment; submersible repeaters; nuclear reactor control systems; medical equipment or systems for life support (e.g. artificial life support devices or systems), surgical implantations, or healthcare intervention (e.g. excision, etc.), and any other applications or purposes that pose a direct threat to human life.
8. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
9. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or system manufactured by you.
10. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
11. This document may not be reproduced or duplicated, in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.

(Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.

(Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

DATA SHEET

MOS FIELD EFFECT TRANSISTOR

NP82N055EHE, NP82N055KHE
NP82N055CHE, NP82N055DHE, NP82N055MHE, NP82N055NHE

SWITCHING
N-CHANNEL POWER MOS FET

DESCRIPTION

These products are N-channel MOS Field Effect Transistors designed for high current switching applications.

<R> **ORDERING INFORMATION**

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
NP82N055EHE-E1-AY Note1, 2	Pure Sn (Tin)	Tape 800 p/reel	TO-263 (MP-25ZJ) typ. 1.4 g
NP82N055EHE-E2-AY Note1, 2			
NP82N055KHE-E1-AY Note1			TO-263 (MP-25ZK) typ. 1.5 g
NP82N055KHE-E2-AY Note1			
NP82N055CHE-S12-AZ Note1, 2	Sn-Ag-Cu	Tube 50 p/tube	TO-220 (MP-25) typ. 1.9 g
NP82N055DHE-S12-AY Note1, 2	Pure Sn (Tin)		TO-262 (MP-25 Fin Cut) typ. 1.8 g
NP82N055MHE-S18-AY Note1			TO-220 (MP-25K) typ. 1.9 g
NP82N055NHE-S18-AY Note1			TO-262 (MP-25SK) typ. 1.8 g

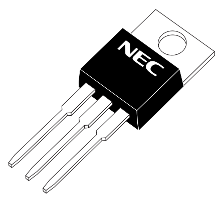
Notes 1. Pb-free (This product does not contain Pb in the external electrode.)

2. Not for new design

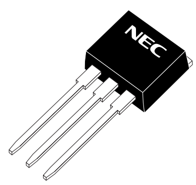
FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance
  $R_{DS(on)}$ = 8.6 mΩ MAX. (V_{GS} = 10 V, I_D = 41 A)
- Low input capacitance
  C_{iss} = 3500 pF TYP.
- Built-in gate protection diode

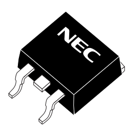
(TO-220)



(TO-262)



(TO-263)



Document No. D14138EJ6V0DS00 (6th edition)
Date Published October 2007 NS
Printed in Japan

The mark <R> shows major revised points.
The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	55	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	±20	V
Drain Current (DC) (T_C = 25°C) Note1	$I_{D(DC)}$	±82	A
Drain Current (pulse) Note2	$I_{D(pulse)}$	±300	A
Total Power Dissipation (T_A = 25°C)	P_T	1.8	W
Total Power Dissipation (T_C = 25°C)	P_T	163	W
Channel Temperature	T_{ch}	175	°C
Storage Temperature	T_{stg}	–55 to +175	°C
Single Avalanche Current Note3	I_{AS}	72/49/17	A
Single Avalanche Energy Note3	E_{AS}	51/240/289	mJ

Notes 1. Calculated constant current according to MAX. allowable channel temperature.

2. PW ≤ 10 μs, Duty cycle ≤ 1%

3. Starting T_{ch} = 25°C, V_{DD} = 28 V, R_G = 25 Ω, V_{GS} = 20 → 0 V (See **Figure 4.**)

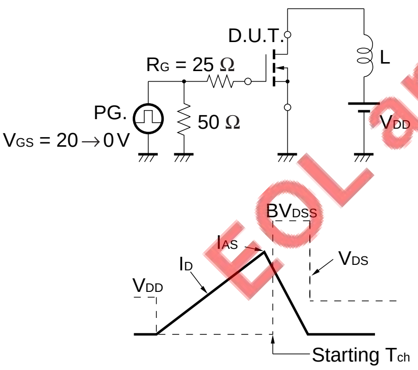
THERMAL RESISTANCE

Channel to Case Thermal Resistance	$R_{th(ch-C)}$	0.92	°C/W
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	83.3	°C/W

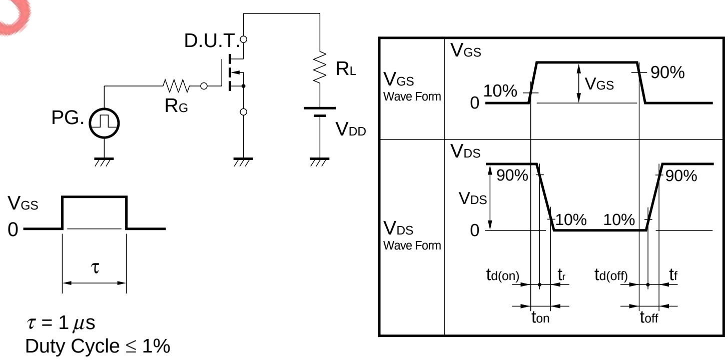
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 55 V, V_{GS} = 0 V			10	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±10	μA
Gate to Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2.0	3.0	4.0	V
Forward Transfer Admittance	$\mid y_{fs} \mid$	V_{DS} = 10 V, I_D = 41 A	19	38		S
Drain to Source On-state Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 41 A		6.9	8.6	mΩ
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz		3500	5250	pF
Output Capacitance	C_{oss}			550	830	pF
Reverse Transfer Capacitance	C_{rss}			270	490	pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 28 V, I_D = 41 A, V_{GS} = 10 V, R_G = 1 Ω		31	69	ns
Rise Time	t_r			18	45	ns
Turn-off Delay Time	$t_{d(off)}$			61	120	ns
Fall Time	t_f			19	47	ns
Total Gate Charge	Q_G	V_{DD} = 44 V, V_{GS} = 10 V, I_D = 82 A		65	100	nC
Gate to Source Charge	Q_{GS}			18		nC
Gate to Drain Charge	Q_{GD}			24		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	I_F = 82 A, V_{GS} = 0 V		1.0		V
Reverse Recovery Time	t_{rr}	I_F = 82 A, V_{GS} = 0 V, di/dt = 100 A/μs		45		ns
Reverse Recovery Charge	Q_{rr}			63		nC

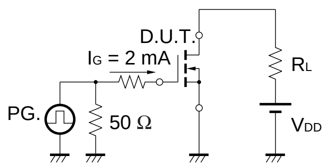
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE



TYPICAL CHARACTERISTICS (T_A = 25°C)

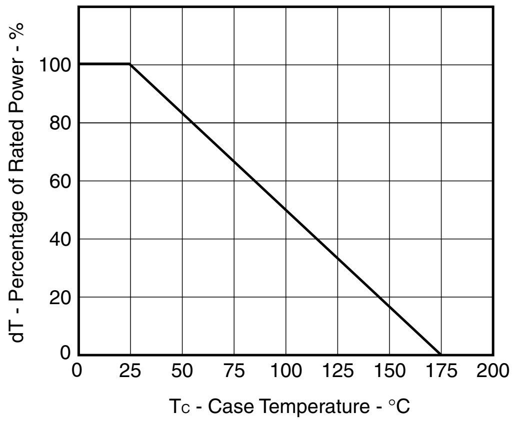


Figure1. DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

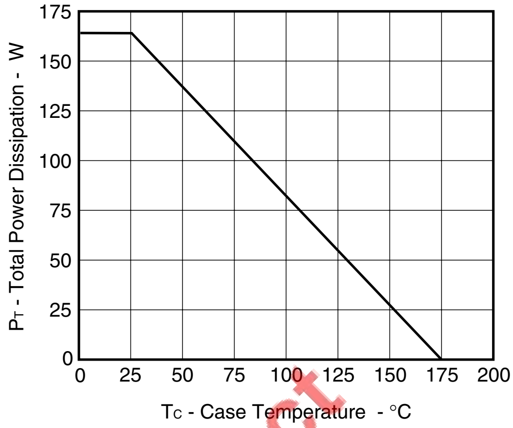


Figure2. TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

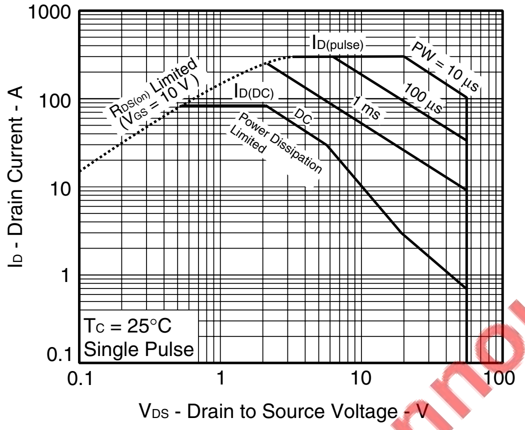


Figure.3 FORWARD BIAS SAFE OPERATING AREA

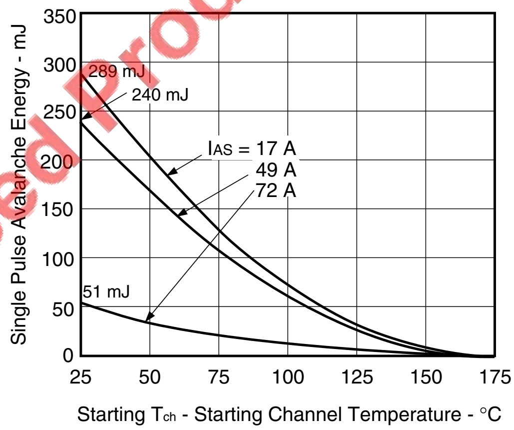


Figure4. SINGLE AVALANCHE ENERGY DERATING FACTOR

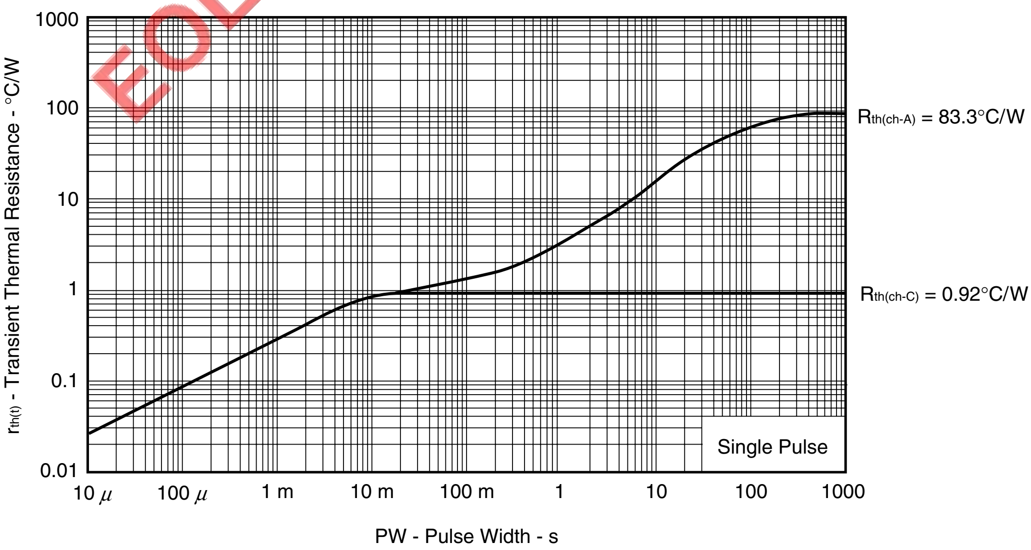


Figure5. TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

Figure6. FORWARD TRANSFER CHARACTERISTICS

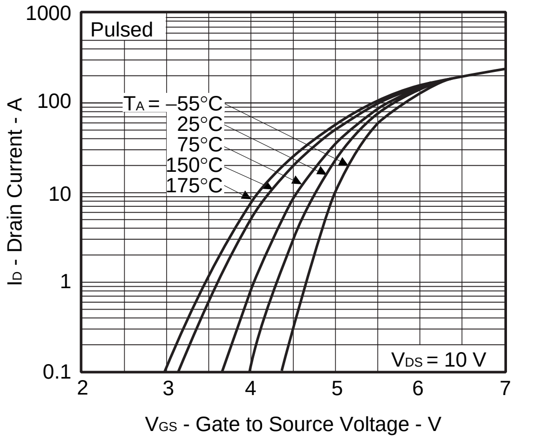


Figure7. DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

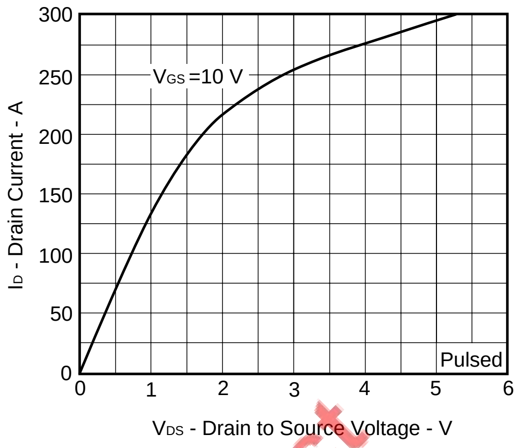


Figure8. FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT

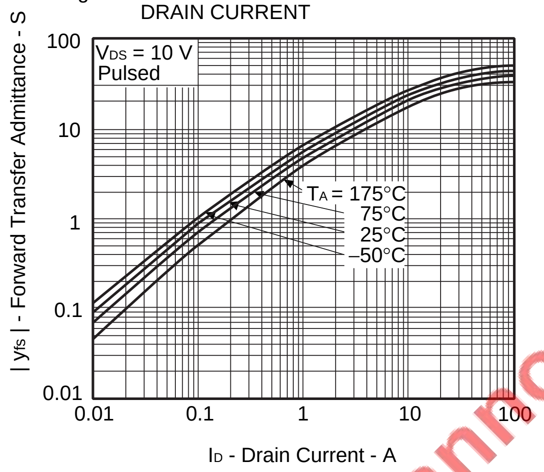


Figure9. DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE

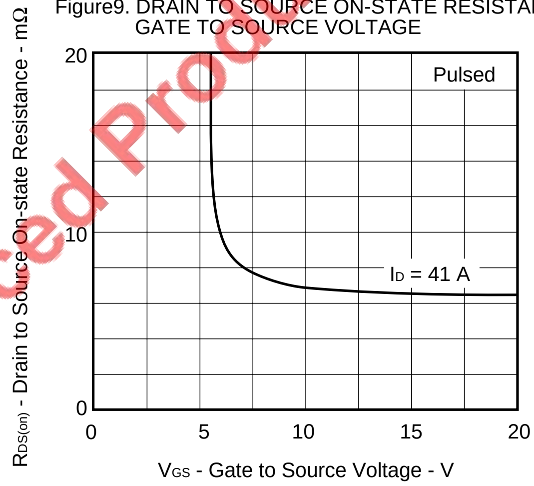


Figure10. DRAIN TO SOURCE ON-STATE
RESISTANCE vs. DRAIN CURRENT

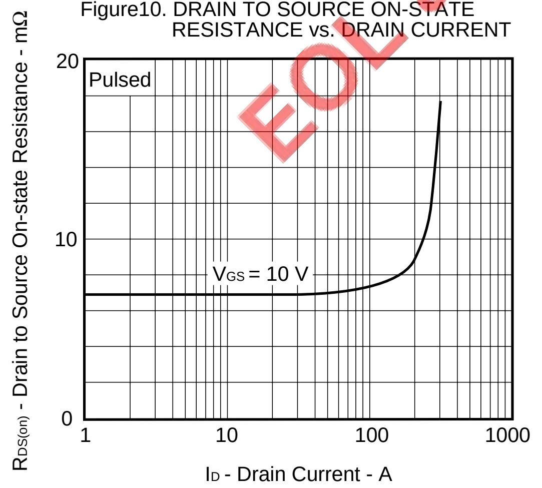


Figure11. GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATURE

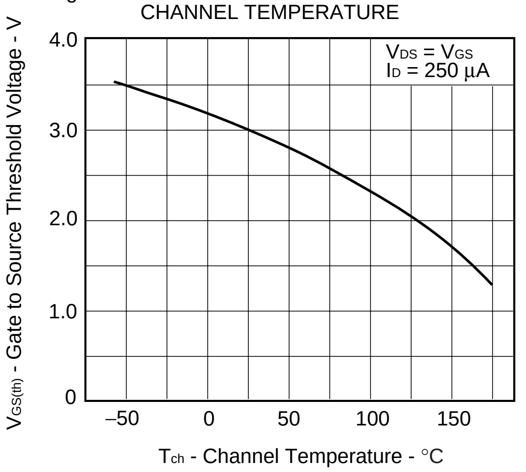


Figure12. DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

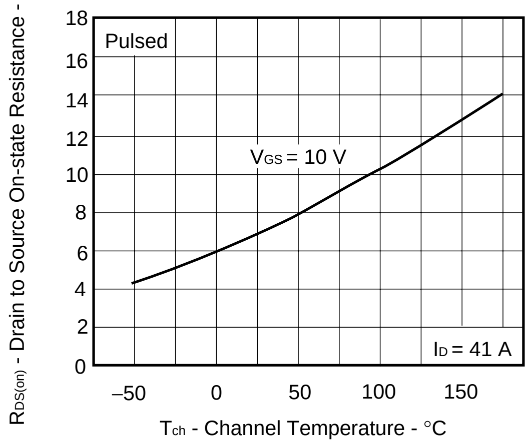


Figure13. SOURCE TO DRAIN DIODE FORWARD VOLTAGE

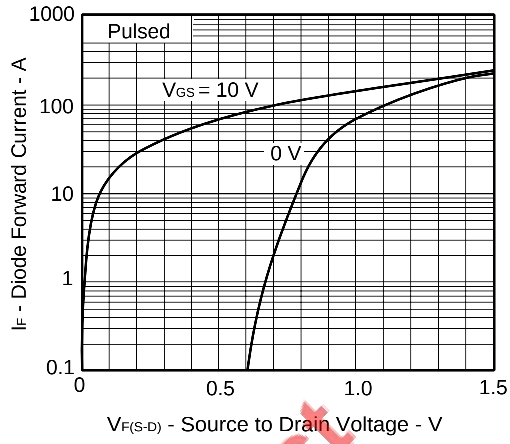


Figure14. CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

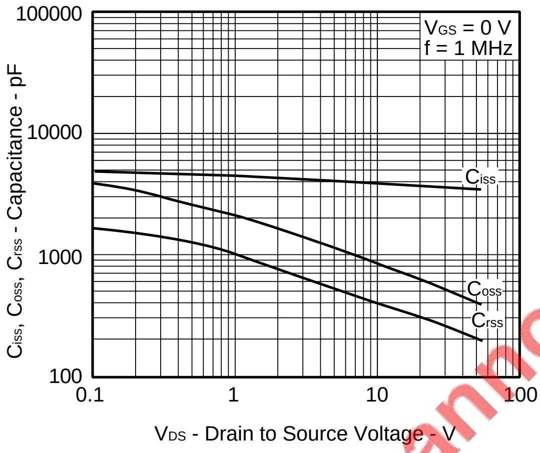


Figure15. SWITCHING CHARACTERISTICS

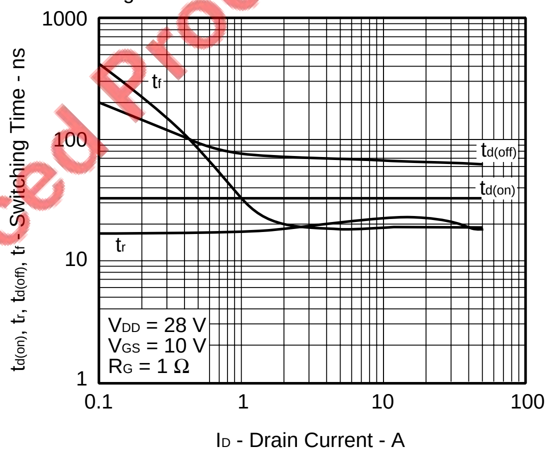


Figure16. REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

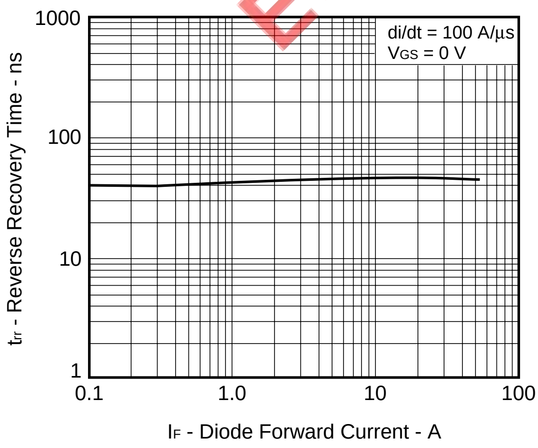
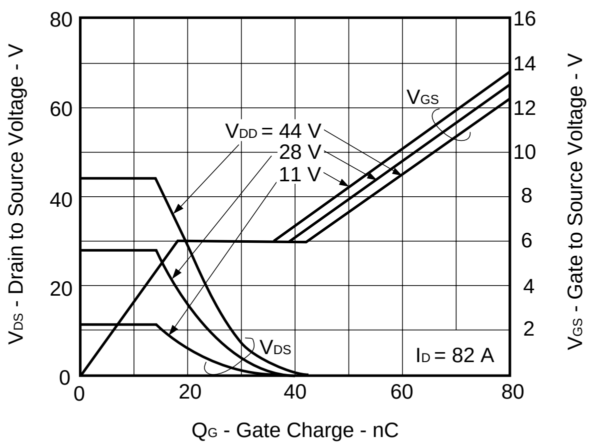
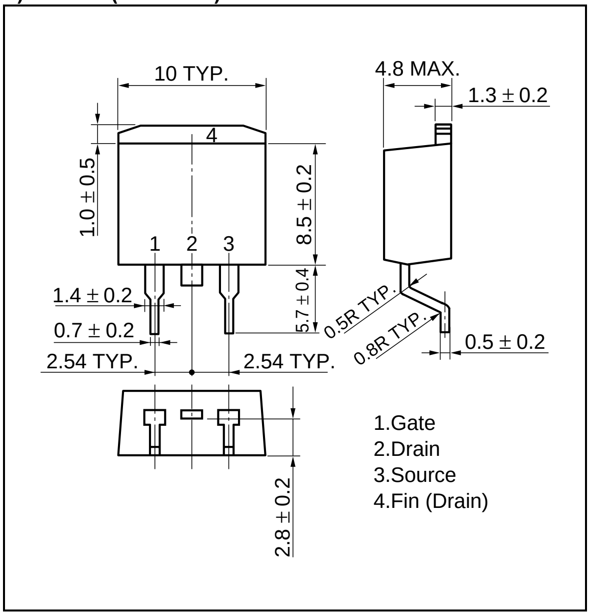


Figure17. DYNAMIC INPUT/OUTPUT CHARACTERISTICS

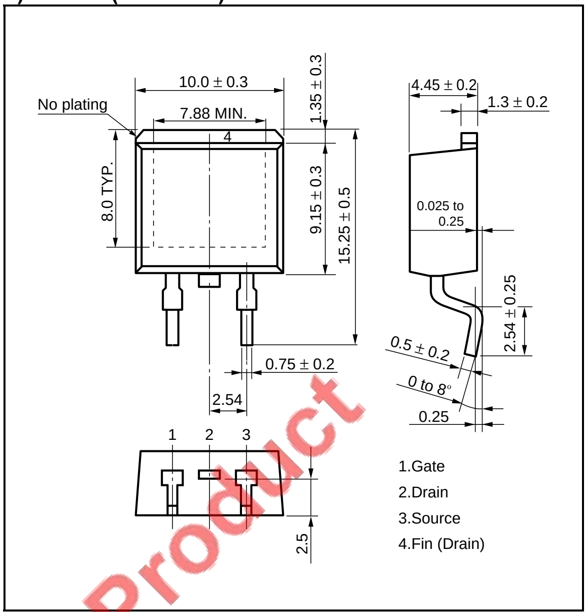


<R> **PACKAGE DRAWINGS (Unit: mm)**

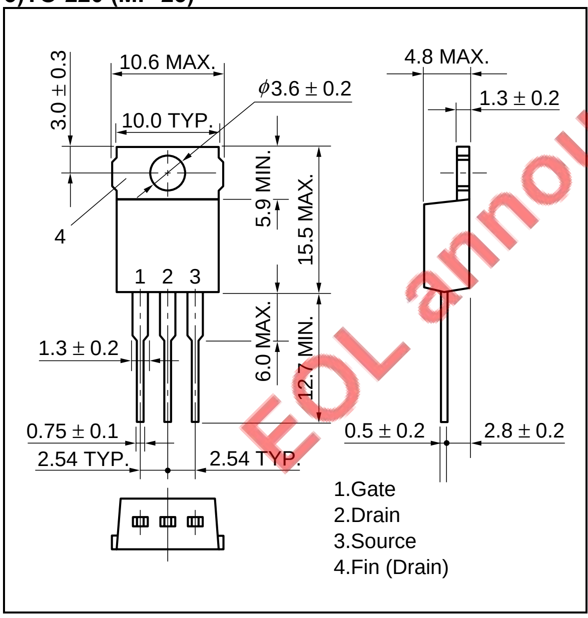
1)TO-263 (MP-25ZJ) Note



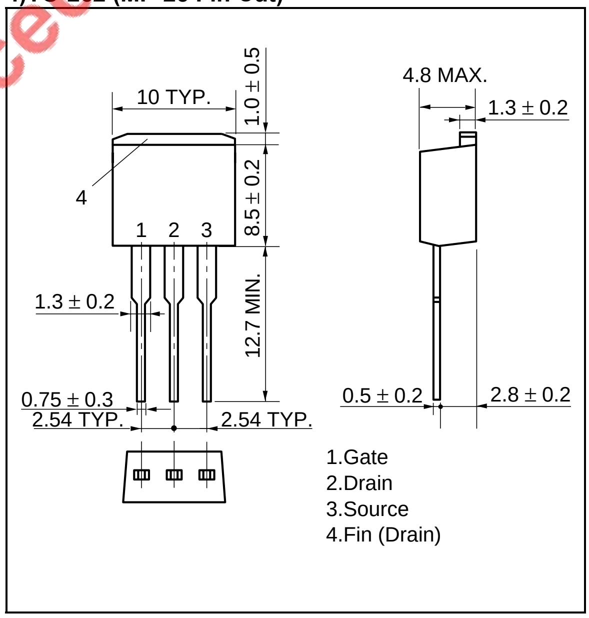
2)TO-263 (MP-25ZK)



3)TO-220 (MP-25) Note

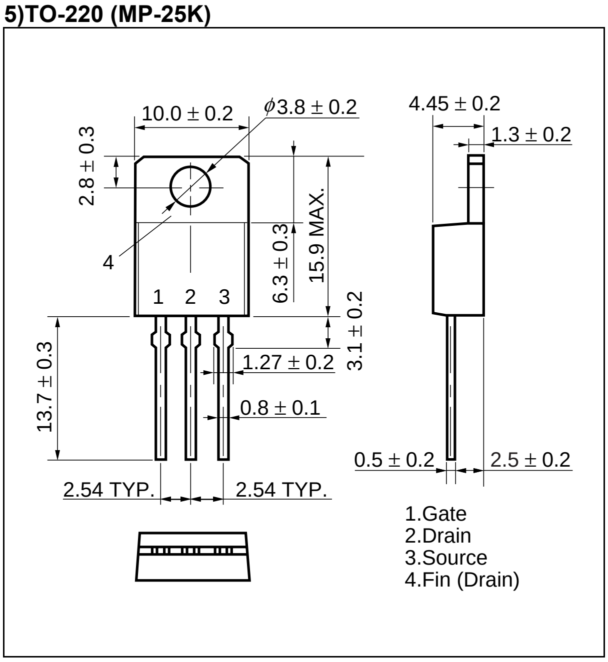


4)TO-262 (MP-25 Fin Cut) Note

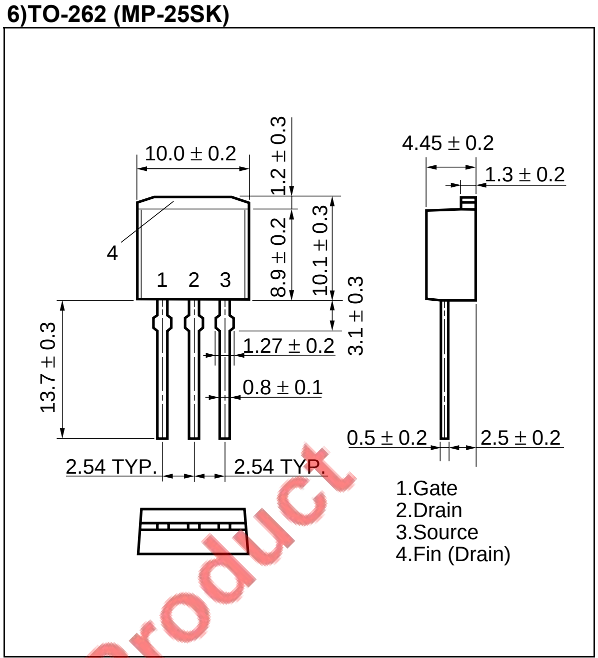


Note Not for new design

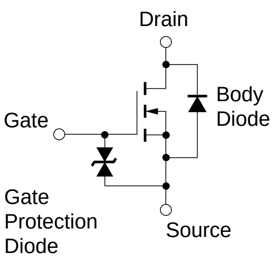
5)TO-220 (MP-25K)



6)TO-262 (MP-25SK)



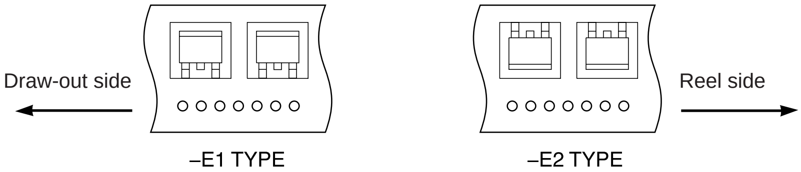
EQUIVALENT CIRCUIT



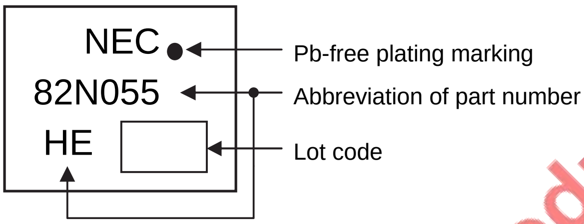
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

<R> **TAPE INFORMATION**

There are two types (-E1, -E2) of taping depending on the direction of the device.



<R> **MARKING INFORMATION**



<R> **RECOMMENDED SOLDERING CONDITIONS**

These products should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow MP-25ZJ, MP-25ZK	Maximum temperature (Package's surface temperature): 260°C or below Time at maximum temperature: 10 seconds or less Time of temperature higher than 220°C: 60 seconds or less Preheating time at 160 to 180°C: 60 to 120 seconds Maximum number of reflow processes: 3 times Maximum chlorine content of rosin flux (percentage mass): 0.2% or less	IR60-00-3
Wave soldering MP-25, MP-25K, MP-25SK, MP-25 Fin Cut	Maximum temperature (Solder temperature): 260°C or below Time: 10 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	THDWS
Partial heating MP-25ZJ, MP-25ZK, MP-25K, MP-25SK	Maximum temperature (Pin temperature): 350°C or below Time (per side of the device): 3 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	P350
Partial heating MP-25, MP-25 Fin Cut	Maximum temperature (Pin temperature): 300°C or below Time (per side of the device): 3 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	P300

Caution Do not use different soldering methods together (except for partial heating).